

Title (en)

Precision high-frequency capacitor formed on semiconductor substrate

Title (de)

Präzisionshochfrequenz-Kondensator auf einem Halbleitersubstrat

Title (fr)

Condensateur haute-fréquence de précision formé sur un substrat semi-conducteur

Publication

EP 1895569 A1 20080305 (EN)

Application

EP 07021796 A 20010913

Priority

- EP 01307796 A 20010913
- US 66148300 A 20000914

Abstract (en)

A precision high-frequency capacitor comprising: a heavily-doped semiconductor substrate having first and second principal surfaces; a first dielectric layer portion formed on the first principal surface of the substrate; a first electrode layer formed on the first dielectric layer portion and electrically insulated from the substrate; a second dielectric layer portion formed on the first principal surface of the substrate; and a second electrode layer formed on the second dielectric layer portion, the second electrode layer being electrically insulated from the substrate and the first electrode layer.

IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

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Designated contracting state (EPC)

DE FR GB

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EP 1189263 A2 20020320; **EP 1189263 A3 20050427**; **EP 1189263 B1 20101124**; CN 1182566 C 20041229; CN 1346138 A 20020424; DE 60143510 D1 20110105; EP 1895568 A1 20080305; EP 1895568 B1 20140716; EP 1895569 A1 20080305; EP 1895569 B1 20130612; JP 2002176106 A 20020621; JP 2007005828 A 20070111; JP 3943879 B2 20070711; JP 5016284 B2 20120905; SG 103315 A1 20040429; TW 535251 B 20030601; US 2003030125 A1 20030213; US 2003057517 A1 20030327; US 6538300 B1 20030325; US 6621142 B2 20030916; US 6621143 B2 20030916

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